

100V N-CHANNEL ENHANCEMENT MODE VERTICAL MOSFET IN SOT223

Product Summary

BV _{DSS}	R _{DS(on)}	Ι _D T _A = +25°C
-60V	$125m\Omega @ V_{GS}=-10V$	-4.3A
	190m Ω @ V_{GS}= -4.5V	-3.5A

Description and Applications

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for highefficiency power management applications.

- DC-DC converters
- Solenoids/relay driver for automotive applications

Features and Benefits

- V_{(BR)DSS} > 100V
- $R_{DS(on)} \le 0.54\Omega @ V_{GS} = 10V$
- Maximum Continuous Drain Current I_D = 1.67A
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotiveproducts/.

• This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

https://www.diodes.com/quality/product-definitions/

 An Automotive-Compliant Part is Available Under Separate Datasheet (<u>ZXMP6A17GQ</u>)

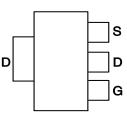
Mechanical Data

- Package: SOT223 (Type DN)
- Package Material: Molded Plastic, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)

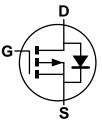


SOT223 (Type DN)

Top View



Pin Out - Top View



Equivalent Circuit

Ordering Information (Note 4)

Part Number	Paakaga	Packing		
Fait Nulliber	Package	Qty.	Carrier	
ZVN4310GTA	SOT223 (Type DN)	1,000	Tape & Reel	

EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

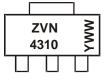
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Notes:



Marking Information



ZVN4310 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 1= 2021) WW or $\overline{W}W$ = Week Code (01~53)

Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	100	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current	I _D	1.67	A
Pulsed Drain Current (Note 6)	I _{DM}	12	A

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 5)	PD	3	W
Thermal Resistance, Junction to Ambient	(Note 5)	R _{0JA}	41.7	°C/W
Thermal Resistance, Junction to Leads	(Note 7)	R _{θJL}	8.84	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)			- 71-				
Drain-Source Breakdown Voltage	BV _{DSS}	100	-	-	V	$V_{GS} = 0V, I_D = 1mA$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	-	-	10 100	μΑ μΑ	$V_{DS} = 100V, V_{GS} = 0V$ $V_{DS} = 80V, V_{GS} = 0V, T_A = +125^{\circ}C$	
Gate-Source Leakage	Igss	-	-	±20	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
On-State Drain Current	I _{D(on)}	9	-	-	А	$V_{GS} = 10V, V_{DS} = 10V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(th)}	1	-	3	V	$V_{DS} = V_{GS}, I_D = 1mA$	
Static Drain-Source On-Resistance	R _{DS(on)}	-	0.4 0.5	0.54 0.75	Ω	V _{GS} = 10V, I _D = 3.3A V _{GS} = 5V, I _D = 1.5A	
Forward Transconductance	g fs	0.6	-	-	S	V _{DS} = 10V, I _D = 3.3A	
DYNAMIC CHARACTERISTICS (Note 8)						·	
Input Capacitance	C _{iss}	-	-	350	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance	Coss	-	-	140	pF		
Reverse Transfer Capacitance	Crss	-	-	20	pF		
Turn-On Delay Time	t _{D(on)}	-	-	8	ns	$V_{DD} = 25V, I_D = 3A, V_{GEN} = 10V,$ $R_{GS} = 50\Omega$	
Turn-On Rise Time	t _R	-	-	25	ns		
Turn-Off Delay Time	t _{D(off)}	-	-	30	ns		
Turn-Off Fall Time	t _F	-	-	16	ns		

Notes: 5. For a device mounted on 50mm X 50mm X 1.6mm FR-4 PCB with high coverage of single sided 2oz copper, in still air condition.

6. Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.

Thermal resistance from junction to solder-point (at the end of the drain lead).
Short duration pulse test used to minimize self-heating effect.



Electrical Characteristics

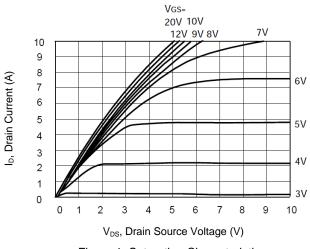


Figure 1. Saturation Characteristics

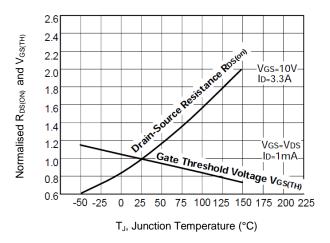


Figure 3. Normalised $R_{\text{DS(ON)}}$ and $V_{\text{GS(TH)}}$ vs. Temperature

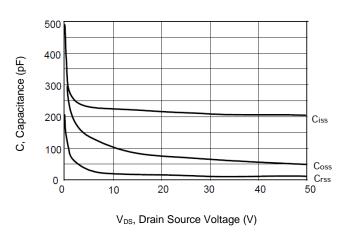


Figure 5. Capacitance vs. Drain-source Voltage

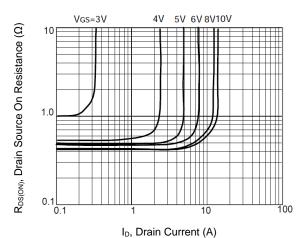


Figure 2. On-resistance vs. Drain Current

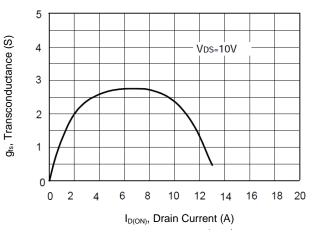


Figure 4. Transconductance vs. Drain Current

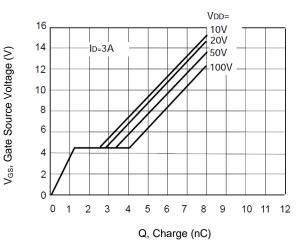
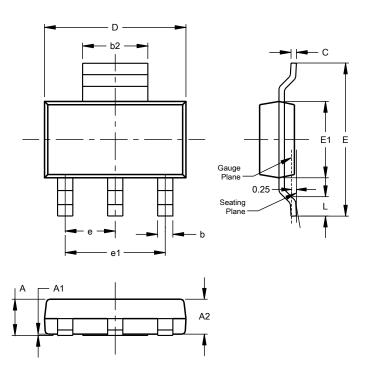


Figure 6. Gate Charge vs. Gate-source Voltage



Package Outline Dimensions

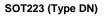
Please see http://www.diodes.com/package-outlines.html for the latest version.



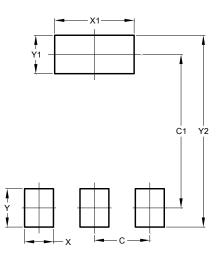
SOT223 (Type DN)					
Dim	Min	Max	Тур		
Α		1.70			
A1	0.01	0.15			
A2	1.50	1.68	1.60		
b	0.60	0.80	0.70		
b2	2.90	3.10			
С	0.20	0.32			
D	6.30	6.70			
E	6.70	7.30			
E1	3.30	3.70			
е			2.30		
e1			4.60		
L	0.85				
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT223 (Type DN)



-	
Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00



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